# 600 Watt Peak Power Zener Transient Voltage Suppressor

### Unidirectional

The NS6A13AT3G is designed to protect voltage sensitive components from high voltage, high energy transients. This device has excellent clamping capability, high surge capability, low zener impedance and fast response time. The NS6A13AT3G is ideally suited for use in computer hard disk drives, communication systems, automotive, numerical controls, process controls, medical equipment, business machines, power supplies, and many other industrial/consumer applications.

### **Specification Features:**

- Peak Reverse Working Voltage of 13 V
- Peak Pulse Power of 600 W (10 x 1000 µsec)
- ESD Rating of Class 3 (>16 kV) per Human Body Model
- ESD Rating of Class 4 (>8 kV) IEC 61000-4-2
- Fast Response Time
- Low Profile Package
- This is a Pb-Free Device

### **Mechanical Characteristics:**

**CASE:** Void-free, transfer-molded, thermosetting plastic

FINISH: All external surfaces are corrosion resistant and leads are

readily Solderable

### **MAXIMUM CASE TEMPERATURE FOR SOLDERING PURPOSES:**

260°C for 10 Seconds

**LEADS:** Modified L-Bend providing more contact area to bond pads

**POLARITY:** Cathode indicated by polarity band

**MOUNTING POSITION:** Any



### ON Semiconductor®

http://onsemi.com

### PLASTIC SURFACE MOUNT ZENER OVERVOLTAGE TRANSIENT SUPPRESSOR





SMA CASE 403D PLASTIC

#### MARKING DIAGRAM



6LG = Specific Device Code

A = Assembly Location

Y = Year

WW = Work Week

■ = Pb-Free Package

### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>		
NS6A13AT3G	SMA (Pb-Free)	5000/Tape & Reel		

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Peak Power Dissipation (Note 1) @ T <sub>L</sub> = 25°C, Pulse Width = 1 ms	P <sub>PK</sub>	600	W
DC Power Dissipation @ $T_L$ = 75°C Measured Zero Lead Length (Note 2) Derate Above 75°C Thermal Resistance from Junction to Lead	P <sub>D</sub> R <sub>θJL</sub>	1.5 20 50	W mW/°C °C/W
DC Power Dissipation (Note 3) @ T <sub>A</sub> = 25°C Derate Above 25°C Thermal Resistance from Junction to Ambient	$P_{D}$ $R_{ hetaJA}$	0.5 4.0 250	W mW/°C °C/W
Forward Surge Current (Note 4) @ T <sub>A</sub> = 25°C	I <sub>FSM</sub>	40	Α
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-65 to +150	°C

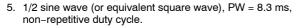
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

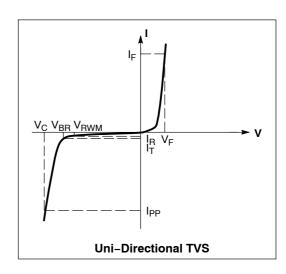
- 1. 10 X 1000 us, non-repetitive.
- 2. 1" square copper pad, FR-4 board
- 3. FR-4 board, using ON Semiconductor minimum recommended footprint, as shown in 403D case outline dimensions spec.
- 4. 1/2 sine wave (or equivalent square wave), PW = 8.3 ms, duty cycle = 4 pulses per minute maximum.

## ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless

otherwise noted, V<sub>F</sub> = 3.5 V Max. @ I<sub>F</sub> (Note 5) = 30 A)

Symbol Parameter			
I <sub>PP</sub>	Maximum Reverse Peak Pulse Current		
V <sub>C</sub>	Clamping Voltage @ I <sub>PP</sub>		
$V_{RWM}$	Working Peak Reverse Voltage		
I <sub>R</sub>	Maximum Reverse Leakage Current @ V <sub>RWM</sub>		
$V_{BR}$	Breakdown Voltage @ I <sub>T</sub>		
I <sub>T</sub>	Test Current		
I <sub>F</sub>	Forward Current		
V <sub>F</sub>	Forward Voltage @ I <sub>F</sub>		





### **ELECTRICAL CHARACTERISTICS**

Device -		V <sub>RWM</sub>		Breakdown Voltage			V <sub>C</sub> @ I <sub>PP</sub> (Note 8)		C <sub>typ</sub>	
		(Note 6) I <sub>R</sub> @ V <sub>RWM</sub>		V <sub>BR</sub> (Note 7) Volts		@ I <sub>T</sub>	V <sub>C</sub>	I <sub>PP</sub>	(Note 9)	
Device	Marking	V	μ <b>Α</b>	Min	Nom	Max	mA	V	Α	рF
NS6A13AT3G	6LG	13	5.0	14.4	15.15	15.9	1.0	21.5	27.9	1160

- 6. A transient suppressor is normally selected according to the working peak reverse voltage (V<sub>RWM</sub>), which should be equal to or greater than the DC or continuous peak operating voltage level.
- 7. V<sub>BR</sub> measured at pulse test current I<sub>T</sub> at an ambient temperature of 25°C.
- 8. Surge current waveform per Figure 1.
- 9. Bias Voltage = 0 V, F = 1 MHz,  $T_J = 25$ °C.

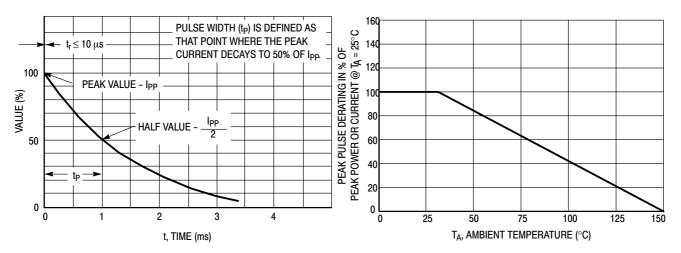
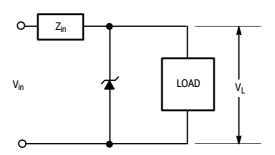


Figure 1. 10  $\times$  1000  $\mu s$  Pulse Waveform

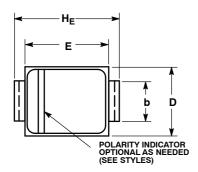
Figure 2. Pulse Derating Curve



**Figure 3. Typical Protection Circuit** 

#### PACKAGE DIMENSIONS

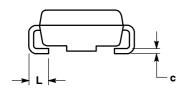
### SMA CASE 403D-02 ISSUE F

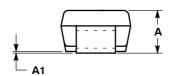


#### NOTES

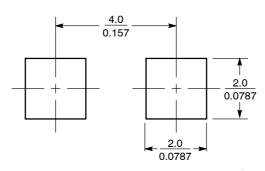
- DIMENSIONING AND TOLERANCING PER ANSI
  VIA 5M 1982
- Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.
- 3. 403D-01 OBSOLETE, NEW STANDARD IS 403D-02.

	М	ILLIMETE	RS	INCHES				
DIM	MIN	NOM	MAX	MIN	NOM	MAX		
Α	1.97	2.10	2.20	0.078	0.083	0.087		
A1	0.05	0.10	0.15	0.002	0.004	0.006		
b	1.27	1.45	1.63	0.050	0.057	0.064		
С	0.15	0.28	0.41	0.006	0.011	0.016		
D	2.29	2.60	2.92	0.090	0.103	0.115		
E	4.06	4.32	4.57	0.160	0.170	0.180		
HE	4.83	5.21	5.59	0.190	0.205	0.220		
L	0.76	1.14	1.52	0.030	0.045	0.060		





### **SOLDERING FOOTPRINT\***



SCALE 8:1  $\left(\frac{\text{mm}}{\text{inches}}\right)$ 

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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